

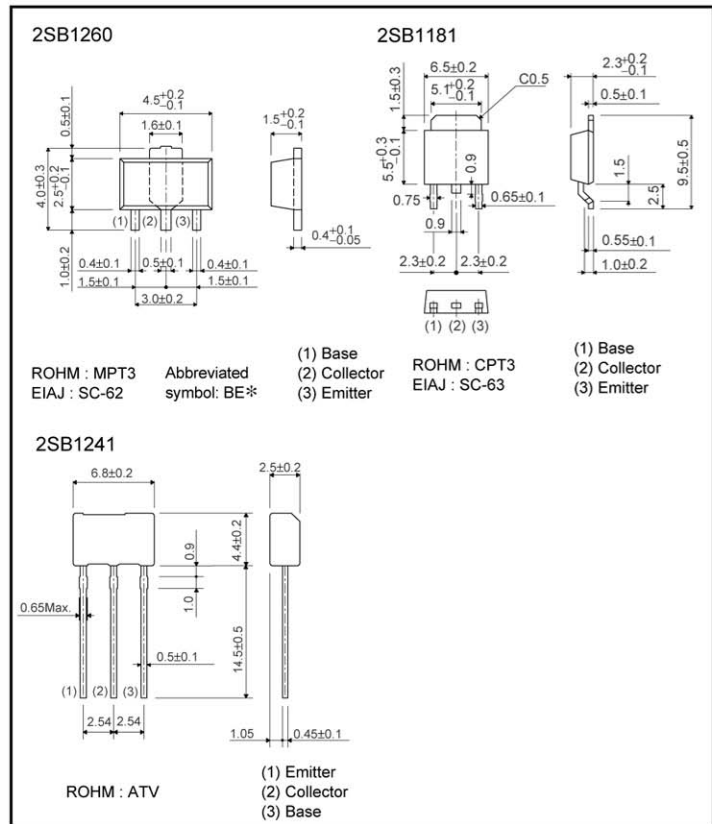
●Features

- 1) High breakdown voltage and high current.  
 $BV_{CEO} = -80V, I_c = -1A$
- 2) Good  $h_{FE}$  linearity.
- 3) Low  $V_{CE(sat)}$ .
- 4) Complements the 2SD1898 / 2SD1863 / 2SD1733.

●Structure

Epitaxial planar type  
 PNP silicon transistor

●External dimensions (Unit : mm)



\* Denotes  $h_{FE}$

●Absolute maximum ratings ( $T_a=25^{\circ}C$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	-80	V
Collector-emitter voltage	$V_{CEO}$	-80	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_c$	-1	A (DC)
	$I_{CP}$	-2 *1	A (Pulse)
Collector power dissipation	Pc	0.5	W
		2 *2	
		1 *3	
		10	W ( $T_c=25^{\circ}C$ )
Junction temperature	$T_j$	150	$^{\circ}C$
Storage temperature	$T_{stg}$	-55 to 150	$^{\circ}C$

\*1 2SB1260 :  $P_w=20ms$  duty=1/2

2SB1241 : Single pulse,  $P_w=100ms$

\*2 2SB1260 : When mounted on a 40x40x0.7 mm ceramic board.

\*3 2SB1241 : Printed circuit board, 1.7mm thick, collector copper plating 100mm<sup>2</sup> or larger.

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● **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	
Collector-base breakdown voltage	BV <sub>CBO</sub>	-80	-	-	V	I <sub>c</sub> = -50μA	
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	-80	-	-	V	I <sub>c</sub> = -1mA	
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> = -50μA	
Collector cutoff current	I <sub>cBO</sub>	-	-	-1	μA	V <sub>CB</sub> = -60V	
Emitter cutoff current	I <sub>EBO</sub>	-	-	-1	μA	V <sub>EB</sub> = -4V	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	-	-	-0.4	V	I <sub>c</sub> /I <sub>B</sub> = -500mA/ -50mA	
DC current transfer ratio	2SB1260, 2SB1181	h <sub>FE</sub>	82	-	390	-	V <sub>CE</sub> = -3V, I <sub>c</sub> = -0.1A
	2SB1241	h <sub>FE</sub>	120	-	390	-	
Transition frequency	2SB1181	f <sub>T</sub>	-	100	-	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> =50mA, f=100MHz
Output capacitance	2SB1260	C <sub>ob</sub>	-	20	-	pF	V <sub>CB</sub> = -10V I <sub>E</sub> =0A f=1MHz
	2SB1181, 2SB1241	C <sub>ob</sub>	-	25	-	pF	

h<sub>FE</sub> values are classified as follows :

Item	P	Q	R
h <sub>FE</sub>	82 to 180	120 to 270	180 to 390

● **Electrical characteristic curves**

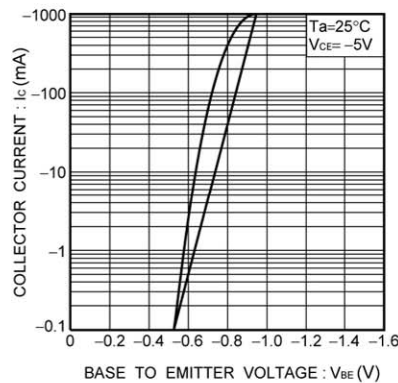


Fig.1 Grounded emitter propagation characteristics

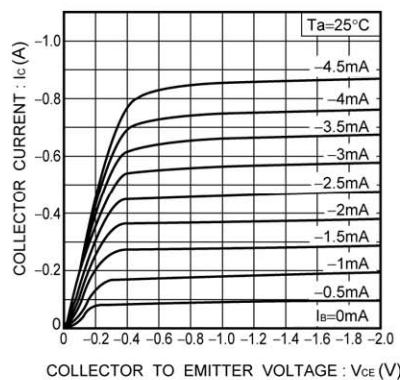


Fig.2 Grounded emitter output characteristics

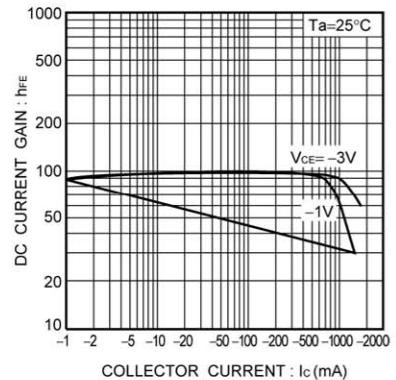


Fig.3 DC current gain vs. collector current

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